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(71) Applicant (for all designated States except US): **ACM RESEARCH (SHANGHAI) INC.** [CN/CN]; Bld. 4, No. 1690 Cailun Road, Zhangjiang High-tech Park, Shanghai 201203 (CN).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **MA, Yue** [US/CN]; Bld. 4, No. 1690 Cailun Road, Zhangjiang High-tech Park, Shanghai 201203 (CN). **WANG, Xi** [CN/CN]; Bld. 4, No. 1690 Cailun Road, Zhangjiang High-tech Park, Shanghai 201203 (CN). **HE, Chuan** [CN/CN]; Bld. 4, No. 1690 Cailun Road, Zhangjiang High-tech Park, Shanghai 201203 (CN). **WANG, Hui** [US/CN]; Bld. 4, No. 1690 Cailun Road, Zhangjiang High-tech Park, Shanghai 201203 (CN).

(74) Agent: **SHANGHAI PATENT & TRADEMARK LAW OFFICE, LLC**; 435 Guiping Road, Xuhui, Shanghai 200233 (CN).

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(54) Title: METHOD FOR SUBSTANTIALLY UNIFORM COPPER DEPOSITION ONTO SEMICONDUCTOR WAFER

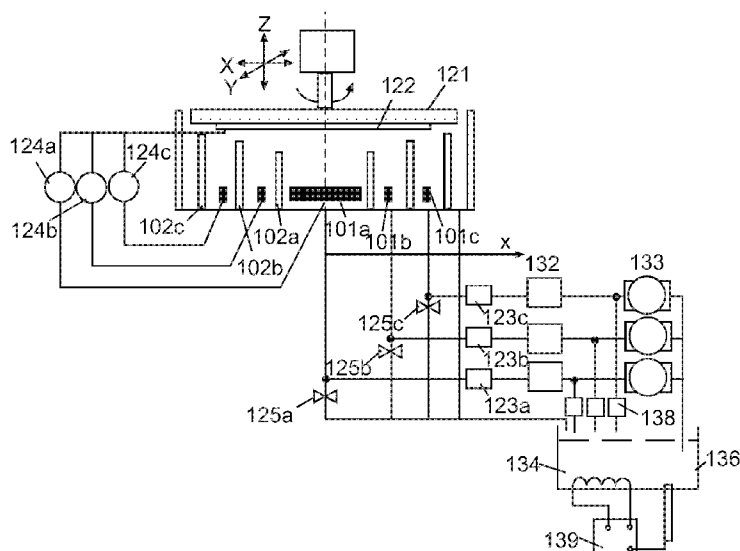


FIG 1

(57) Abstract: The methods practiced in an electrochemical deposition apparatus with two or more electrodes, described in earlier inventions, are disclosed. The methods produce uniform copper films with WFNU less than 2.5% on semiconductor wafers bearing a resistive copper seed layer with a thickness ranging from 50 to 900Å in a copper sulfate based electrolyte whose conductivity is between 0.02 to 0.8S/cm.